I Claim:

1. An alkaline composition for stripping or cleaning integrated circuit substrates, comprising:

(a) one or more bases; and

(b) one or more metal halide compounds of the formula:

$$W_zMX_y$$

where M is a metal selected from the group consisting of Si, Ge, Sn, Pt, P, B, Au, Ir, Os, Cr, Ti, Zr, Rh, Ru, and Sb; X is a halide selected from the group consisting of F, Cl, Br and I; W is selected from the group consisting of H, an alkali or alkaline earth metal, and a metal ion-free hydroxide base moiety; y is a numeral of from 4 to 6 depending on the metal halide; and z is a numeral of from 1, 2 or 3.

2. A composition according to claim 1 wherein the composition is an aqueous, alkaline composition.

3. The composition of Claim 2 wherein the base component (a) is a metal ion-free bases and the base is present in the composition in an amount sufficient to produce a pH of the composition of from about 10 to about 13.

4. The composition of Claim 2 wherein the one or more metal halide compounds is present in the composition an amount of from about 0.5% to about 10% by weight of the composition.

5. The composition of claim 1 wherein the base component (a) is selected from the group consisting of ammonium hydroxide, quaternary ammonium hydroxides and diamines.

6. The composition of claim 5 wherein the base component (a) is a tetraalkyl ammonium hydroxide containing alkyl groups of from 1 to 4 carbon atoms.

7. The composition of claim 2 wherein M is selected from the group consisting of Si, Ge, Zr and Sb.

8. The composition of claim 4 wherein M is selected from the group consisting of Si, Ge, Zr and Sb.

9. The composition of claim 6 wherein M is selected from the group consisting of Si, Ge, Zr and Sb.

10. The composition of claim 7 wherein the metal halide is selected from the group consisting of H_2SiF_6, H_2GeF_6, $((CH_3)_4N)_2GeF_6$, $((CH_3)_4N)_2SiF_6$, $(NH_4)_2SiF_6$ and $(NH_4)_2GeF_6$.

11. The composition of claim 8 wherein the metal halide is selected from the group consisting of H_2SiF_6, H_2GeF_6, $((CH_3)_4N)_2GeF_6$, $((CH_3)_4N)_2SiF_6$, $(NH_4)_2SiF_6$ and $(NH_4)_2GeF_6$.

12. The composition of claim 9 wherein the metal halide is selected from the group consisting of H_2SiF_6, H_2GeF_6, $((CH_3)_4N)_2GeF_6$, $((CH_3)_4N)_2SiF_6$, $(NH_4)_2SiF_6$ and $(NH_4)_2GeF_6$.

13. The composition of claim 10 wherein the metal halide is H_2SiF_6.

14. The composition of claim 11 wherein the metal halide is H_2SiF_6.

15. The composition of claim 12 wherein the metal halide is H_2SiF_6.

16. The composition of claim 1 additionally comprising one or more additional components selected from the group consisting of organic solvents and co-solvents, metal chelating or complexing agents, silicates, fluorides, additional metal corrosion inhibitors, surfactants, titanium residue removal enhancing agents, oxidizing agents and bath stabilizing agents.

17. The composition of claim 2 additionally comprising one or more additional components selected from the group consisting of organic solvents and co-solvents, metal chelating or complexing agents, silicates, fluorides, additional metal corrosion inhibitors, surfactants, titanium residue removal enhancing agents, oxidizing agents and bath stabilizing agents.

18. The composition of claim 4 additionally comprising one or more additional components selected from the group consisting of organic solvents and co-solvents, metal chelating or complexing agents, silicates, fluorides, additional metal corrosion inhibitors, surfactants, titanium residue removal enhancing agents, oxidizing agents and bath stabilizing agents.

19. A composition of claim 16 comprising tetramethylammonium hydroxide, trans-(1,2-cyclohexylenedinitrilo)tetraacetic acid, hydrogen peroxide, dihydrogen hexafluorosilicate and water.

20. The composition of claim 19 having a pH of about 11.5.

21. A composition of claim 16 comprising tetramethylammonium hydroxide, trans-(1,2-cyclohexylenedinitrilo)tetraacetic acid, hydrogen peroxide, dihydrogen hexafluorogermanate and water.

22. The composition of claim 21 having a pH of about 11.5.

23. A composition of claim 16 comprising tetramethylammonium hydroxide, trans-(1,2-cyclohexylenedinitrilo)tetraacetic acid, hydrogen peroxide, ammonium hexafluorogermanate and water.

24. The composition of claim 23 having a pH of about 11.5.

25. A method for cleaning semiconductor wafer substrates, comprising:
contacting a semiconductor wafer substrate having a substrate surface for a time and at a temperature sufficient to clean unwanted contaminants and residues from said substrate surface with a composition comprising the composition of claim 1.

26. The method of claim 25 wherein the composition is a composition of claim 2.

27. The method of claim 25 wherein the composition is a composition of claim 3.

28. The method of claim 25 wherein the composition is a composition of claim 4.

29. The method of claim 25 wherein the composition is a composition of claim 5.

30. The method of claim 25 wherein the composition is a composition of claim 6.

31. The method of claim 25 wherein the composition is a composition of claim 7.

32. The method of claim 25 wherein the composition is a composition of claim 8.

33. The method of claim 25 wherein the composition is a composition of claim 9.

34. The method of claim 25 wherein the composition is a composition of claim 10.

35. The method of claim 25 wherein the composition is a composition of claim 11.

36. The method of claim 25 wherein the composition is a composition of claim 12.

37. The method of claim 25 wherein the composition is a composition of claim 13.

38. The method of claim 25 wherein the composition is a composition of claim 14.

39. The method of claim 25 wherein the composition is a composition of claim 15.

40. The method of claim 25 wherein the composition is a composition of claim 16.

41. The method of claim 25 wherein the composition is a composition of claim 17.

42. The method of claim 25 wherein the composition is a composition of claim 18.

43. The method of claim 25 wherein the composition is a composition of claim 19.

44. The method of claim 25 wherein the composition is a composition of claim 20.

45. The method of claim 25 wherein the composition is a composition of claim 21.

46. The method of claim 25 wherein the composition is a composition of claim 23.

47. The method of claim 25 wherein the composition is a composition of claim 23.

48. The method of claim 25 wherein the composition is a composition of claim 24.